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(30) Priority:	(71) Applicant: <b>OKAMOTO MACHINE WORKS LTD</b>
(43) Date of application publication: <b>12.09.00</b>	(72) Inventor: <b>YAMADA TSUTOMU KUBO TOMIO</b>
(84) Designated contracting states:	(74) Representative:

**(54) POLISHING PAD**

(57) Abstract:

PROBLEM TO BE SOLVED: To provide a CMP polishing pad excellent in heat resistance and providing a wafer excellent in thickness uniformity with small step difference between an insulating film and a metallic layer.

*Jeiss*

SOLUTION: This polishing pad is used to polish a wafer by pressing the polishing pad to the wafer surface and rotating a spindle of a wafer chucking mechanism and a spindle of the polishing pad to slidngly rub the rotating polishing pad against the rotating wafer surface. In this case, a resin surface layer, slidngly rubbing against the wafer surface, of the polishing pad contains 5-50 wt.% of boehmite abrasive grain of 0.1  $\mu\text{m}$  or less in grain diameter.

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